IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Arup Bhattacharyya

Title: HIGH-PERFORMANCE ONE-TRANSISTOR MEMORY CELL

Docket No.: 1303.111US1
Filed: July 2, 2003
Examiner: Unknown

Serial No.: 10/612793
Due Date: N/A
Group Art Unit: 2811

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

We are transmitting herewith the following attached items (as indicated with an "X"):

X A return postcard.
X A Communication Concerning Related Applications (1 pg.).
X An Information Disclosure Statement (2 pgs.), Form 1449 (2 pgs.), and copies of 20 cited documents.

If not provided for in a separate paper filed herewith, Please consider this a PETITION FOR EXTENSION OF TIME for sufficient number of months to enter these papers and please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
Customer Number 21186

By: Marvin L Beekman
Atty: Marvin L. Beekman
Reg. No. 38,377

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 25th day of February, 2004.

Judy Dent
Name

Judy Dent
Signature

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
(GENERAL)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Arup Bhattacharyya	Examiner: Unknown
Serial No.:	10/612793	Group Art Unit: 2811
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Title:	HIGH-PERFORMANCE ONE-TRANSISTOR MEMORY CELL	

COMMUNICATION CONCERNING RELATED APPLICATION(S)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Applicant would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

Serial/Patent No.	Filing Date	Attorney Docket	Title
10/232855	August 30, 2002	1303.072US1	GATED LATERAL THYRISTOR-BASED RANDOM ACCESS MEMORY CELL (GLTRAM)
10/232848	August 30, 2002	1303.073US1	ONE-DEVICE NON-VOLATILE RANDOM ACCESS MEMORY CELL
10/232846	August 30, 2002	1303.080US1	ONE TRANSISTOR SOI NON-VOLATILE RANDOM ACCESS MEMORY CELL
10/425483	April 29, 2003	1303.105US1	ONE TRANSISTOR SOI NON-VOLATILE RANDOM ACCESS MEMORY CELL

Respectfully submitted,

ARUP BHATTACHARYYA

By Applicant's Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
P.O. Box 2938
Minneapolis, MN 55402
(612) 373-6960

Date 2-25-04 By Marvin L. Beekman
Marvin L. Beekman
Reg. No. 38,377

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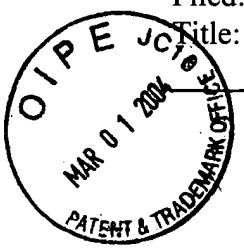
Judith Dent
Name

Judith Dent
Signature

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Arup Bhattacharyya	Examiner:	Unknown
Serial No.:	10/612793	Group Art Unit:	2811
Filed:	July 02, 2003	Docket:	1303.111US1
Title:	HIGH-PERFORMANCE ONE-TRANSISTOR MEMORY CELL		



INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicant respectfully requests that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicant requests that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicant with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 19-0743 in order to have this Information Disclosure Statement considered.

The present application is either a U.S. national patent application filed after June 30, 2003 or an international application that entered the national stage under 35 U.S.C. § 371 after June 30, 2003. Thus, Applicant believes that the U.S. Patent & Trademark Office has waived the requirement under 37 C.F.R. 1.98 (a)(2)(i) for submitting a copy of each cited U.S. patent and each U.S. patent application publication. The waiver is provided in a pre-OG notice from the U.S. Patent & Trademark Office entitled "Information Disclosure Statements May Be Filed Without Copies of U.S. Patents and Published Applications in Patent Applications filed after June 30, 2003" and dated July 11, 2003. Applicant acknowledges the requirement to submit copies of foreign patent documents and non-patent literature in accordance with 37 C.F.R. 1.98(a)(2).

The Examiner is invited to contact the Applicant's Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

ARUP BHATTACHARYYA

By his Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
P.O. Box 2938
Minneapolis, MN 55402
(612) 373-6960

Date 2-25-04 By _____
Marvin L. Beekman
Reg. No. 38,377

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Judith Dent
Name

Judith Dent
Signature

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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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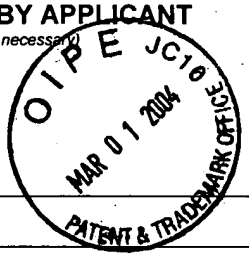

Complete if Known	
Application Number	10/612793
Filing Date	July 2,2003
First Named Inventor	Bhattacharyya,Arup
Group Art Unit	2811
Examiner Name	Unknown

Sheet 1 of 2

Attorney Docket No: 1303.111US1

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
	US-2003/0042534	03/06/2003	Bhattacharyya,Arup,et al.	257	317	08/30/2001
	US-2003/0072126	04/17/2003	Bhattacharyya,Arup	361	311	08/30/2001
	US-2003/0089942	05/15/2003	Bhattacharyya,Arup	257	310	11/09/2001
	US-2003/0151948	08/14/2003	Bhattacharyya,Arup,et al.	365	185.18	02/12/2002
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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T[2]
	JP-61-166078	07/26/1986	Ariga,R.	H01L	29/78	

EXAMINER **DATE CONSIDERED**

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered,whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

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Application Number	10/612793
Filing Date	July 2,2003
First Named Inventor	Bhattacharyya,Arup
Group Art Unit	2811
Examiner Name	Unknown

Sheet 2 of 2

Attorney Docket No: 1303.111US1

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No [1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog,etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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